

*Amend A2*

Semiconductor Devices and A Method for Providing the Same;" and Serial No. 10,034067 (filed 12/28/2001), entitled "Buried Power Buss Utilized as A Sinker for High Current, High Power Semiconductor Devices and A Method for Providing the Same"; assigned to the assignee of the present application, and filed on the same date.

---

Please replace the paragraph beginning at page 19, line 15, with the following rewritten paragraph:

---

*A2*

A method and system for providing an interconnect on a semiconductor device is disclosed. This method, called the buried power buss results in lower interconnect sheet resistance versus standard approaches. The method provides additional capability since it results in oxide isolation in place of junction isolation and allows the long junction isolation process to be eliminated. Oxide isolation results in lower leakage and capacitance than the standard junction isolation. This approach results in the metal having an oxide jacket thus allowing metal to be connected while isolating itself from other circuit functions. The method provides a superior connection from the collector or drain of active devices to the buried layer thus allowing the standard sinker masking and diffusion process to be dropped; while providing a lower Ron (on resistance). The method provides direct contact of the metal grounding to the substrate lowering the Ron of active devices and lowering ground noise. This grounded, oxide isolated buried power bus provides ground isolated epitaxial islands of active and passive elements that need to be circuit isolated from each other. All of these advantages come with reduced masking steps while eliminating long high temperature processes. If the epitaxial layer to be utilized is below a thickness of 6um this approach allows for the buried layer masking and diffusion to be dropped from the process providing an additional cost savings.

---